

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

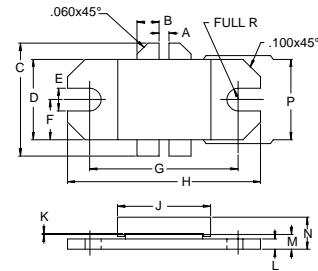
The **ASI TVU100** is Designed for Television Band IV & V Applications up to 860 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 8.5$  dB at 100 W/860 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	10 A
$V_{CB}$	60 V
$V_{CE}$	35 V
$P_{DISS}$	140 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.0 °C/W

**PACKAGE STYLE .450 BAL FLG(A)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.055 / 1.40
B	.120 / 3.05	.130 / 3.30
C		.785 / 19.94
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F		.230 / 5.84
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N		.195 / 4.95
P	.445 / 11.30	.455 / 11.56

**ORDER CODE: ASI10651**
**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	35			V
$BV_{CER}$	$I_C = 50$ mA $R_{BE} = 10$ Ω	60			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CES}$	$V_E = 28$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
$P_{GE}$	$V_{CE} = 25$ V $I_{CQ} = 2 \times 100$ mA $f = 860$ MHz $P_{OUT} = 100$ W	8.5			dB